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Kind regards,

Team Nexperia

# PEMD15; PUMD15

NPN/PNP resistor-equipped transistors;  
R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

Rev. 4 — 19 December 2011

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP complement	NPN/NPN complement	Package configuration
	NXP	JEITA			
PEMD15	SOT666	-	PEMB15	PEMH15	ultra small and flat lead
PUMD15	SOT363	SC-88	PUMB15	PUMH15	very small

### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor; for the PNP transistor (TR2) with negative polarity</b>						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	



## 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

## 3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMD15	-	plastic surface-mounted package; 6 leads	SOT666
PUMD15	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD15	5E
PUMD15	D0*

[1] \* = placeholder for manufacturing site code

**5. Limiting values**

**Table 6. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor; for the PNP transistor (TR2) with negative polarity</b>						
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V	
V <sub>I</sub>	input voltage TR1					
	positive		-	+30	V	
	negative		-	-10	V	
	input voltage TR2					
	positive		-	+10	V	
	negative		-	-30	V	
I <sub>O</sub>	output current		-	100	mA	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	PEMD15 (SOT666)		[1][2]	-	200	mW
	PUMD15 (SOT363)		[1]	-	200	mW
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	PEMD15 (SOT666)		[1][2]	-	300	mW
	PUMD15 (SOT363)		[1]	-	300	mW
T <sub>j</sub>	junction temperature		-	150	°C	
T <sub>amb</sub>	ambient temperature		-65	+150	°C	
T <sub>stg</sub>	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.



## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMD15 (SOT666)		[1][2]	-	625	K/W
	PUMD15 (SOT363)		[1]	-	625	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMD15 (SOT666)		[1][2]	-	417	K/W
	PUMD15 (SOT363)		[1]	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.



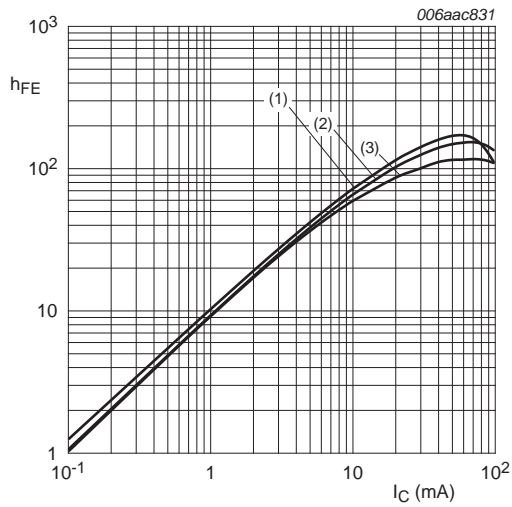
## 7. Characteristics

**Table 8. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

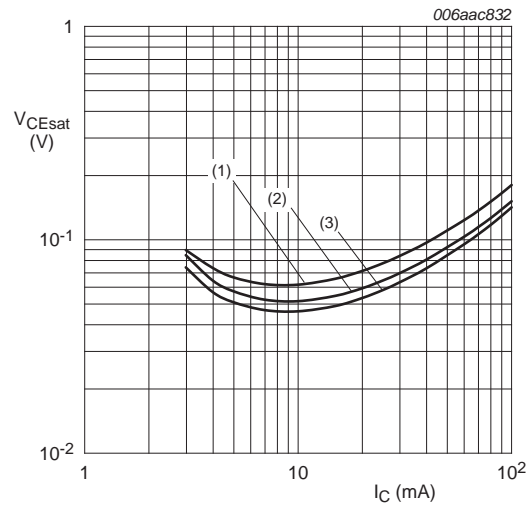
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor; for the PNP transistor (TR2) with negative polarity</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	$\mu\text{A}$
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	900	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}$	30	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ }\mu\text{A}$	-	1.1	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 20\text{ mA}$	2.5	1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF
$f_T$	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	[1]			
	TR1 (NPN)		-	230	-	MHz
	TR2 (PNP)		-	180	-	MHz

[1] Characteristics of built-in transistor



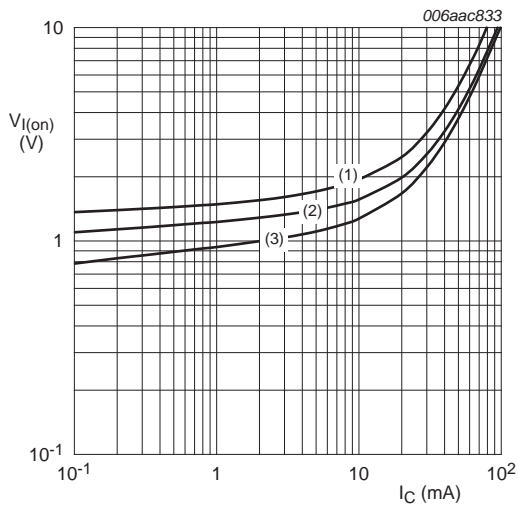
- $V_{CE} = 5\text{ V}$
- (1)  $T_{amb} = 100\text{ }^\circ\text{C}$
  - (2)  $T_{amb} = 25\text{ }^\circ\text{C}$
  - (3)  $T_{amb} = -40\text{ }^\circ\text{C}$

**Fig 4. TR1 (NPN): DC current gain as a function of collector current; typical values**



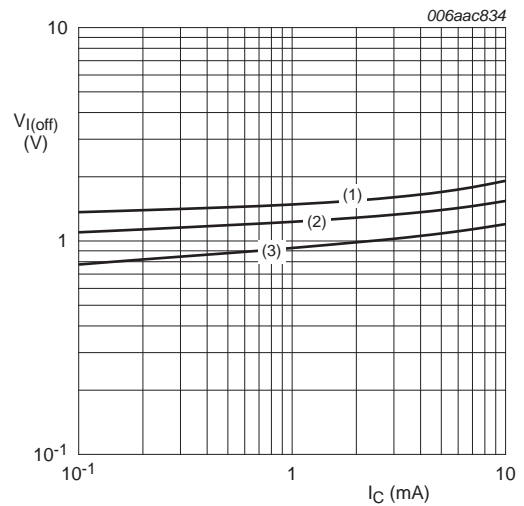
- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ }^\circ\text{C}$
  - (2)  $T_{amb} = 25\text{ }^\circ\text{C}$
  - (3)  $T_{amb} = -40\text{ }^\circ\text{C}$

**Fig 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values**



- $V_{CE} = 0.3\text{ V}$
- (1)  $T_{amb} = -40\text{ }^\circ\text{C}$
  - (2)  $T_{amb} = 25\text{ }^\circ\text{C}$
  - (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

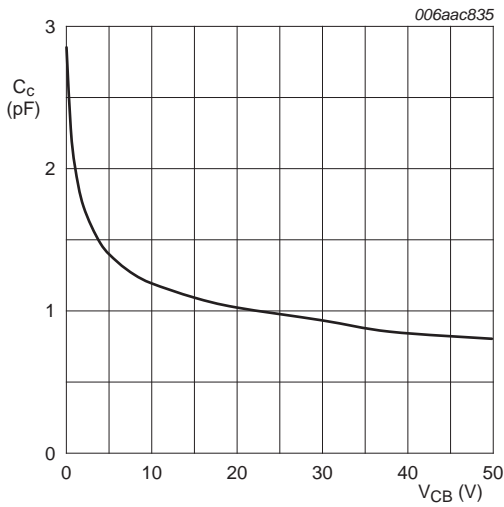
**Fig 6. TR1 (NPN): On-state input voltage as a function of collector current; typical values**



- $V_{CE} = 5\text{ V}$
- (1)  $T_{amb} = -40\text{ }^\circ\text{C}$
  - (2)  $T_{amb} = 25\text{ }^\circ\text{C}$
  - (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig 7. TR1 (NPN): Off-state input voltage as a function of collector current; typical values**





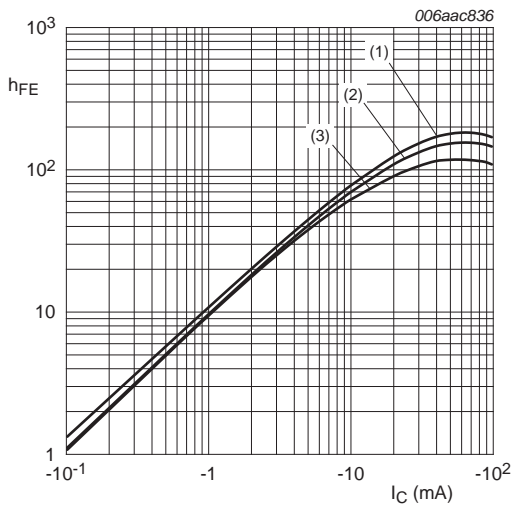
$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

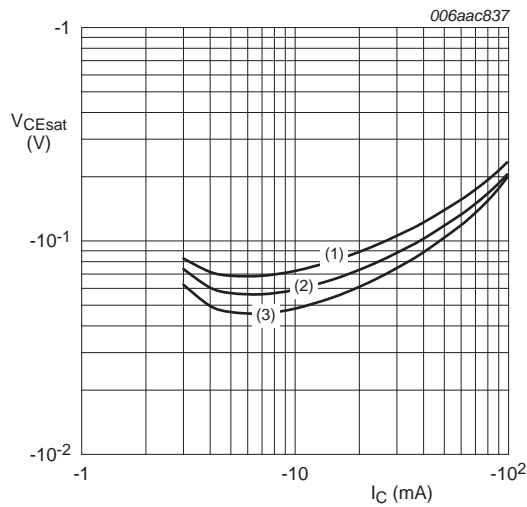
Fig 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



$V_{CE} = -5 \text{ V}$

- (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

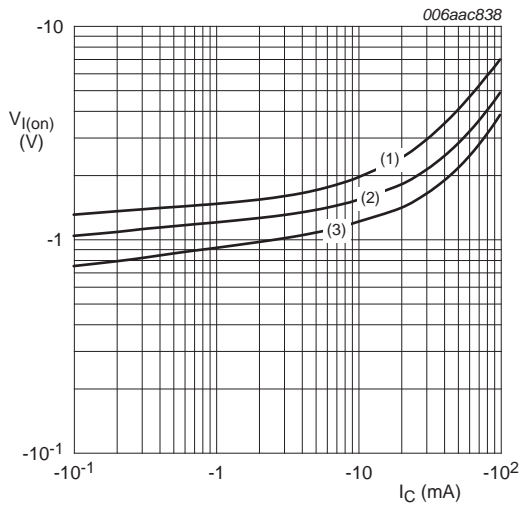
Fig 10. TR2 (PNP): DC current gain as a function of collector current; typical values



$I_C/I_B = 20$

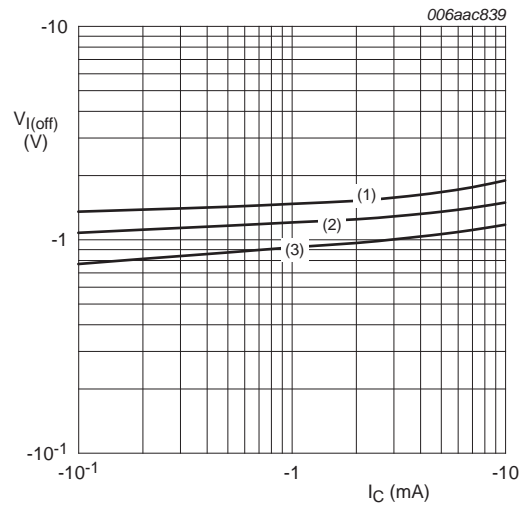
- (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 11. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



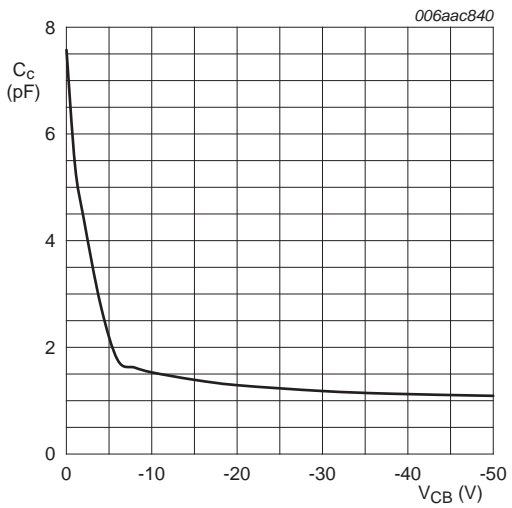
$V_{CE} = -0.3 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 12. TR2 (PNP): On-state input voltage as a function of collector current; typical values**



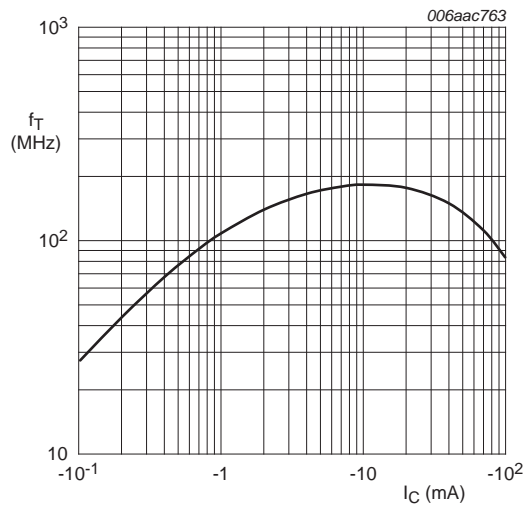
$V_{CE} = -5 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 13. TR2 (PNP): Off-state input voltage as a function of collector current; typical values**



$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 14. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values**



$V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

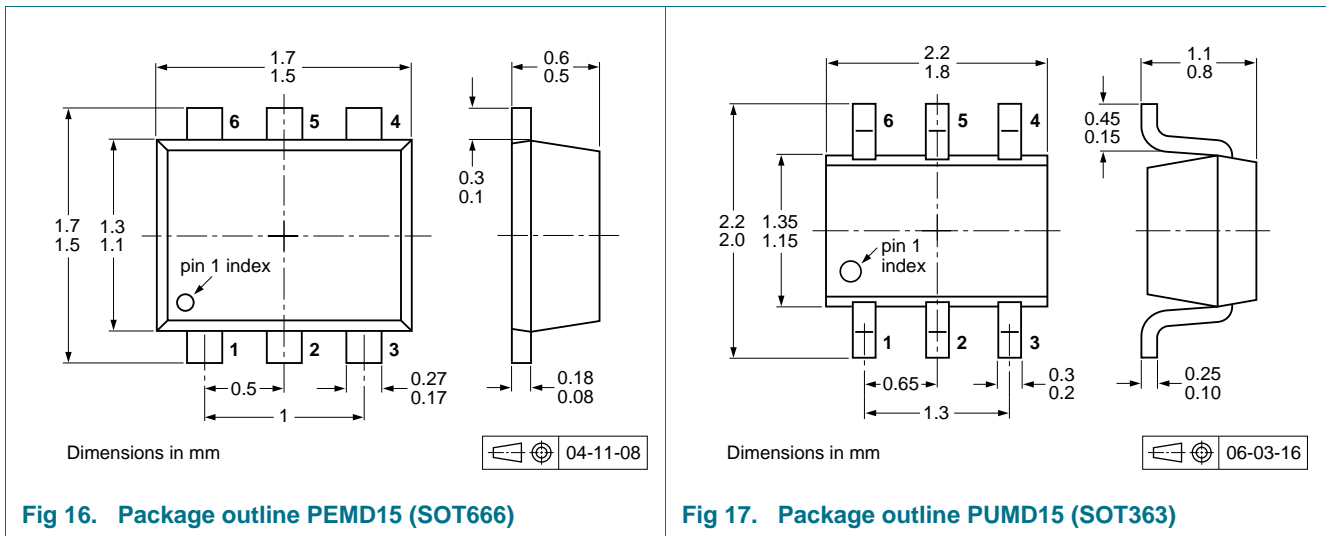
**Fig 15. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor**

**8. Test information**

**8.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**9. Package outline**



**10. Packing information**

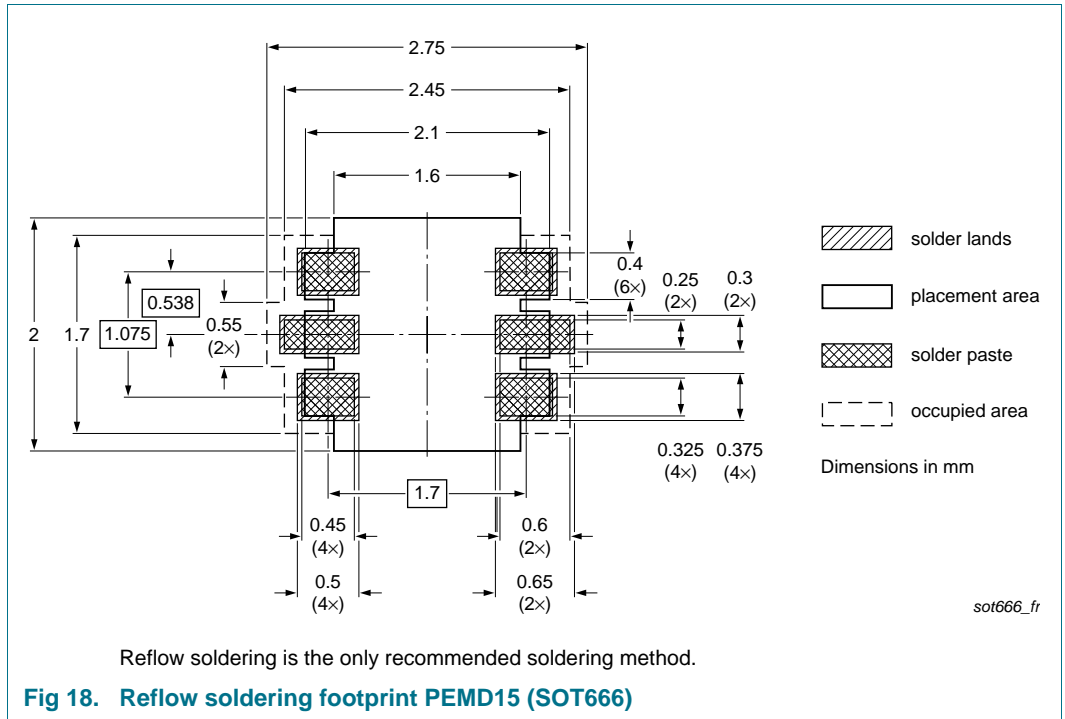
**Table 9. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMD15	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMD15	SOT363	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 14](#).  
 [2] T1: normal taping  
 [3] T2: reverse taping

## 11. Soldering



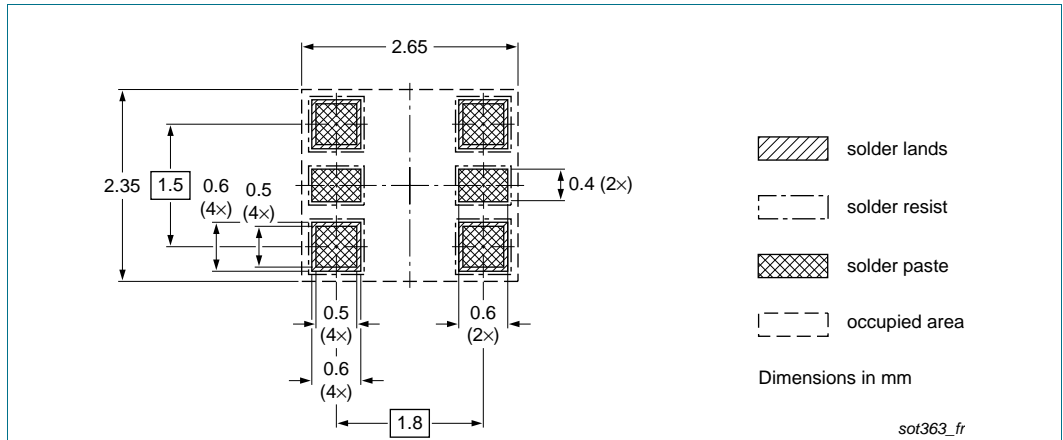


Fig 19. Reflow soldering footprint PUMD15 (SOT363)

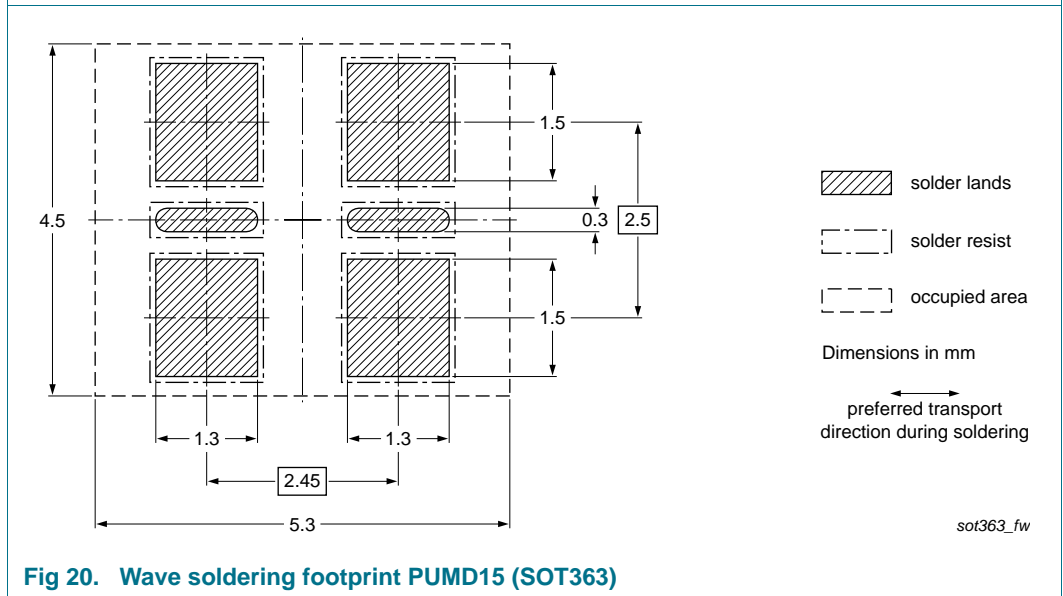


Fig 20. Wave soldering footprint PUMD15 (SOT363)

## 12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD15_PUMD15 v.4	20111219	Product data sheet	-	PEMD15_PUMD15 v.3
Modifications:	<ul style="list-style-type: none"> <li>• <a href="#">Section 1 "Product profile"</a>: updated</li> <li>• <a href="#">Section 4 "Marking"</a>: updated</li> <li>• <a href="#">Figure 1 to 3, 8, 9, 14 and 15</a>: added</li> <li>• <a href="#">Section 6 "Thermal characteristics"</a>: updated</li> <li>• <a href="#">Figure 4 to 7, 10 to 13</a>: updated</li> <li>• <a href="#">Table 8 "Characteristics"</a>: I<sub>CEO</sub> updated, f<sub>T</sub> added</li> <li>• <a href="#">Section 8 "Test information"</a>: added</li> <li>• <a href="#">Section 11 "Soldering"</a>: added</li> <li>• <a href="#">Section 13 "Legal information"</a>: updated</li> </ul>			
PEMD15_PUMD15 v.3	20090902	Product data sheet	-	PEMD15_PUMD15 v.2
PEMD15_PUMD15 v.2	20050425	Product data sheet	-	PUMD15 v.1
PUMD15 v.1	20040204	Product specification	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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